ON Semiconductor

Is Now



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Noninverting 3-State Buffer

MC74VHC1G126, MC74VHC1GT126

The MC74VHC1G126 / MC74VHC1GT126 is a single gate noninverting 3-state buffer in tiny footprint packages. The MC74VHC1G126 has CMOS-level input thresholds while the MC74VHC1GT126 has TTL-level input thresholds.

The internal circuit is composed of three stages, including a buffered 3-state output which provides high noise immunity and stable output.

The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when V_{CC} = 0 V and when the output voltage exceeds $V_{CC}.$ These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Designed for 2.0 V to 5.5 V V_{CC} Operation
- 3.5 ns t_{PD} at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A, SC-74A, TSOP-5, SOT-553, SOT-953 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

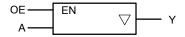
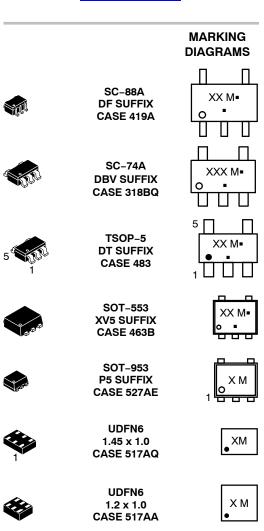


Figure 1. Logic Symbol



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XX = Specific Device Code
M = Date Code*
= Pb-Free Package

UDFN6

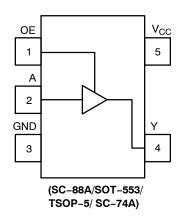
1.0 x 1.0 CASE 517BX

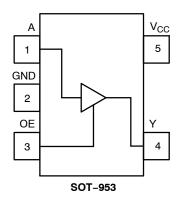
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 8 of this data sheet.

XM





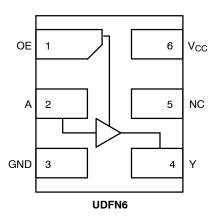


Figure 2. Pinout (Top View)

(SC-88A/SOT-553/ TSOP-5/SC-74A)

PIN ASSIGNMENT

Pin	Function		
1	OE		
2	А		
3	GND		
4	Y		
5	V _{CC}		

PIN ASSIGNMENT (SOT-953)

Pin	Function
1	А
2	GND
3	OE
4	Y
5	V _{CC}

PIN ASSIGNMENT (UDFN)

Pin	Function
1	OE
2	Α
3	GND
4	Υ
5	NC
6	V _{CC}

FUNCTION TABLE

Inp	Output	
OE	Α	Υ
Н	L	L
Н	Н	Н
L	Х	Z

X = Don't Care

MAXIMUM RATINGS

Symbol	Characteri	stics	Value	Unit
V _{CC}	DC Supply Voltage SC-74A, S	TSOP-5, SC-88A (NLV) C-88A, UDFN6, SOT-553, SOT-953	-0.5 to +7.0 -0.5 to +6.5	V
V_{IN}	DC Input Voltage SC-74A, S	TSOP-5, SC-88A (NLV) C-88A, UDFN6, SOT-553, SOT-953	-0.5 to +7.0 -0.5 to +6.5	V
V _{OUT}	DC Output Voltage TSOP-5, SC-88A (NLV)	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
	DC Output Voltage SC-74A, SC-88A, UDFN6, SOT-553, SO	Active-Mode (High or Low State) T-953 Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +6.5 -0.5 to +6.5	V
I _{IK}	DC Input Diode Current	-20	mA	
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-20	mA
l _{OUT}	DC Output Source/Sink Current		±25	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Grou	±50	mA	
T _{STG}	Storage Temperature Range	-65 to +150	°C	
TL	Lead Temperature, 1 mm from Case for 10	secs	260	°C
T_J	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SC-88A SC-74A SOT-553 SOT-953 UDFN6	377 320 324 254 154	°C/W
P _D	Power Dissipation in Still Air	SC-88A SC-74A SOT-553 SOT-953 UDFN6	332 390 386 491 812	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)		± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Applicable to devices with outputs that may be tri-stated.
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22–A115–A (Machine Model) be discontinued per JEDEC/JEP172A.

4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol		Min	Max	Unit	
V _{CC}	Positive DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	TSOP-5, SC-88A (NLV)	0	V _{CC}	V
	DC Output Voltage	SC-74A, SC-88A, UDFN6, SOT-553, SOT-953 Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V_{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Ran	ge	-55	+125	°C
t _r , t _f	Input Rise and Fall Time	TSOP-5, SC-88A (NLV) $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0	100 20	ns/V
	Input Rise and Fall Time	SC-74A, SC-88A, UDFN6, SOT-553, SOT-953 $V_{CC}=2.0\ V$ $V_{CC}=2.3\ V\ to\ 2.7\ V$ $V_{CC}=3.0\ V\ to\ 3.6\ V$ $V_{CC}=4.5\ V\ to\ 5.5\ V$	0 0 0 0	20 20 10 5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (MC74VHC1G126)

		Test	Vcc	7	Γ _A = 25°	С	-40°C ≤	Γ _A ≤ 85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input		2.0	1.5	_	-	1.5	-	1.5	-	V
	Voltage		3.0	2.1	_	-	2.1	_	2.1	-	1
			4.5	3.15	-	-	3.15	_	3.15	-	1
			5.5	3.85	_	_	3.85	-	3.85	_	1
V _{IL}	Low-Level Input		2.0	-	-	0.5	-	0.5	-	0.5	V
	Voltage		3.0	_	_	0.9	-	0.9	-	0.9	1
			4.5	-	-	1.35	=	1.35	-	1.35	1
			5.5	_	_	1.65	-	1.65	-	1.65	1
V _{OH}	High-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -4 m\text{A} \\ &I_{OH} = -8 m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.58 3.94	2.0 3.0 4.5 –	- - - -	1.9 2.9 4.4 2.48 3.80	- - - -	1.9 2.9 4.4 2.34 3.66	- - - -	V
V _{OL}	Low-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 - -	0.1 0.1 0.1 0.36 0.36		0.1 0.1 0.1 0.44 0.44	- - - -	0.1 0.1 0.1 0.52 0.52	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	2.0 to 5.5	_	_	±0.1	-	±1.0	-	±1.0	μА
I _{OZ}	3-State Output Leakage Current	V _{OUT} = 0 V to 5.5 V	5.5	-	-	±0.25	-	±2.5	_	± 2.5	μΑ
l _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	_	-	1.0	-	10	_	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	_	_	1.0	_	20	-	40	μΑ

DC ELECTRICAL CHARACTERISTICS (MC74VHC1GT126)

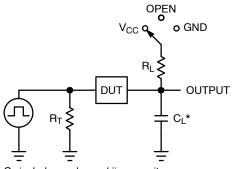
		Test	V _{CC}	1	_A = 25°	C	-40°C ≤	T _A ≤ 85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input		2.0	1.0	-	-	1.0	-	1.0	-	V
	Voltage		3.0	1.4	-	-	1.4	-	1.4	-	1
			4.5	2.0	-	-	2.0	-	2.0	-	1
			5.5	2.0	_	-	2.0	-	2.0	-	1
V_{IL}	Low-Level Input		2.0	-	-	0.28	-	0.28	-	0.28	V
	Voltage		3.0	-	-	0.45	=	0.45	-	0.45]
			4.5	-	ı	0.8	-	0.8	-	0.8]
			5.5	-	-	0.8	_	0.8	-	0.8	
V _{OH}	High-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -4 m\text{A} \\ &I_{OH} = -8 m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.58 3.94	2.0 3.0 4.5 –	- - - -	1.9 2.9 4.4 2.48 3.80	- - - -	1.9 2.9 4.4 2.34 3.66	- - - -	V
V _{OL}	Low-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 -	0.1 0.1 0.1 0.36 0.36		0.1 0.1 0.1 0.44 0.44	- - - -	0.1 0.1 0.1 0.52 0.52	V
I _{IN}	Input Leakage Cur- rent	V _{IN} = 5.5 V or GND	2.0 to 5.5	-	-	±0.1	-	±1.0	_	±1.0	μΑ
I _{OZ}	3-State Output Leakage Current	V _{OUT} = 0 V to 5.5 V	5.5	_	-	±0.25	-	±2.5	-	±2.5	μА
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	_	-	1.0	-	10	-	10	μА
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	-	-	1.0	-	20	_	40	μА
I _{CCT}	Increase in Quies- cent Supply Current per Input Pin	One Input: V _{IN} = 3.4 V; Other Input at V _{CC} or GND	5.5	-	I	1.35	-	1.5	-	1.65	mA

AC ELECTRICAL CHARACTERISTICS

				T	A = 25°	С	-40°C ≤ 7	Γ _A ≤ 85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay,	C _L = 15 pF	3.0 to 3.6	_	4.5	8.0	-	9.5	_	12.0	ns
t _{PHL}	A to Y (Figures 3 and 4)	C _L = 50 pF		_	6.4	11.5	-	13.0	-	16.0	
	,	C _L = 15 pF	4.5 to 5.5	_	3.5	5.5	-	6.5	_	8.5	
		C _L = 50 pF		_	4.5	7.5	-	8.5	-	10.5	
t _{PZL} ,	Output Enable	C _L = 15 pF	3.0 to 3.6	-	4.5	8.0	-	9.5	_	11.5	ns
t _{PZH}	Time, OE to Y (Figures 3 and 4)	C _L = 50 pF		_	6.4	11.5	-	13.0	_	15.0	
	,	C _L = 15 pF	4.5 to 5.5	-	3.5	5.1	-	6.0	-	8.5	
		C _L = 50 pF		_	4.5	7.1	-	8.0	_	10.5	
t _{PLZ} ,	Output Disable	C _L = 15 pF	3.0 to 3.6	-	6.5	9.7	-	11.5	-	14.5	ns
t _{PHZ}	Time, OE to Y (Figures 3 and 4)	C _L = 50 pF		_	8.0	13.2	-	15.0	-	18.0	
	,	C _L = 15 pF	4.5 to 5.5	-	4.8	6.8	-	8.0	-	10.0	
		C _L = 50 pF		_	7.0	8.8	-	10.0	-	12.0	
C _{IN}	Input Capacitance			-	4.0	10	-	10	-	10	pF
C _{OUT}	Output Capacitance	Output in High Impedance State		-	6.0	I	-	-	-	-	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 5)	8.0	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



Test	Switch Position	C _L , pF	R_L, Ω
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table	Χ
t _{PLZ} / t _{PZL}	V _{CC}		1 k
t _{PHZ} / t _{PZH}	GND		1 k

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 Ω) f = 1 MHz

Figure 3. Test Circuit

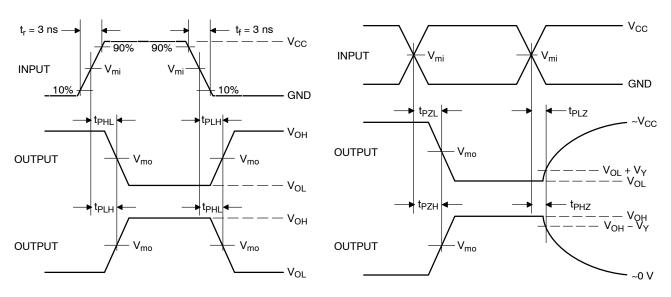


Figure 4. Switching Waveforms

		V _m		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t_{PZL} , t_{PLZ} , t_{PZH} , t_{PHZ}	V _Y , V
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

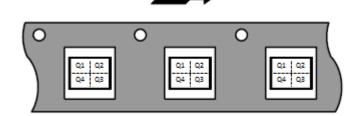
ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
M74VHC1G126DFT1G	SC-88A	W2	Q2	3000 / Tape & Reel
M74VHC1G126DFT2G	SC-88A	W2	Q4	3000 / Tape & Reel
NLVVHC1G126DFT1G*	SC-88A	W2	Q2	3000 / Tape & Reel
NLVVHC1G126DFT2G*	SC-88A	W2	Q4	3000 / Tape & Reel
M74VHC1GT126DF1G	SC-88A	W3	Q2	3000 / Tape & Reel
M74VHC1GT126DF2G	SC-88A	W3	Q4	3000 / Tape & Reel
NLVVHC1GT126DF2G*	SC-88A	W3	Q4	3000 / Tape & Reel
NLVVHC1GT126DF1G*	SC-88A	W3	Q2	3000 / Tape & Reel
MC74VHC1G126DBVT1G	SC-74A	W2	Q4	3000 / Tape & Reel
MC74VHC1GT126DBVT1G	SC-74A	W3	Q4	3000 / Tape & Reel
M74VHC1G126DTT1G	TSOP-5	W2	Q4	3000 / Tape & Reel
M74VHC1GT126DT1G	TSOP-5	W3	Q4	3000 / Tape & Reel
NLVVHC1GT126DT1G*	TSOP-5	W3R	Q4	3000 / Tape & Reel
MC74VHC1G126XV5T2G (In Development)	SOT-553	TBD	Q4	4000 / Tape & Reel
MC74VHC1GT126XV5T2G (In Development)	SOT-553	TBD	Q4	4000 / Tape & Reel
MC74VHC1G126P5T5G	SOT-953	J	Q2	8000 / Tape & Reel
MC74VHC1GT126P5T5G	SOT-953	R	Q2	8000 / Tape & Reel
MC74VHC1G126MU1TCG (In Development)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
MC74VHC1GT126MU1TCG	UDFN6, 1.45 x 1.0, 0.5P	T (Rotated 270° CW)	Q4	3000 / Tape & Reel
MC74VHC1GT126MU2TCG	UDFN6, 1.2 x 1.0, 0.4P	9	Q4	3000 / Tape & Reel
MC74VHC1G126MU3TCG (In Development)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel
MC74VHC1GT126MU3TCG	UDFN6, 1.0 x 1.0, 0.35P	R (Rotated 180° CW)	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel

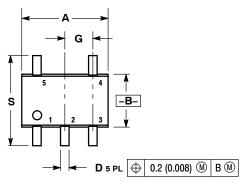
Direction of Feed

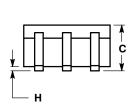


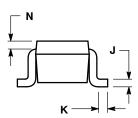
^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE L



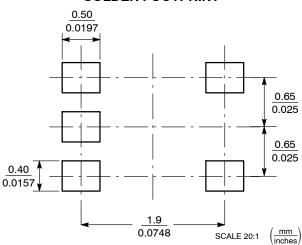




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
C	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	0.026 BSC		0.65 BSC	
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008 REF		0.20 REF		
S	0.079	0.087	2 00	2 20	

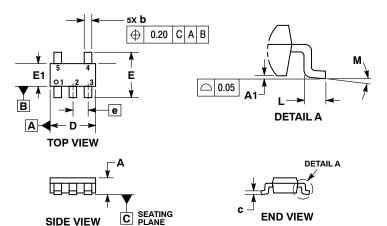
SOLDER FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

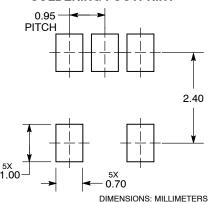
SC-74A CASE 318BQ **ISSUE B**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.90	1.10	
A1	0.01	0.10	
b	0.25	0.50	
С	0.10	0.26	
D	2.85	3.15	
E	2.50	3.00	
E1	1.35	1.65	
е	0.95 BSC		
L	0.20	0.60	
М	0° 10°		

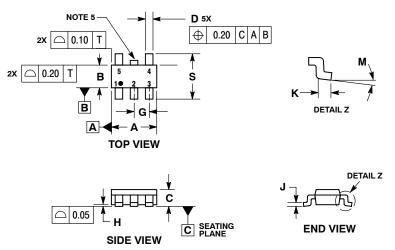
RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 **ISSUE M**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

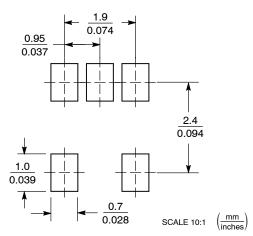
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.

 5. OPTIONAL CONSTRUCTION: AN ADDITIONAL
- OPTIONAL CONSTRUCTION: AN ADDITIONAL
 TRIMMED LEAD IS ALLOWED IN THIS LOCATION.
 TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2
 FROM BODY.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.85	3.15	
В	1.35	1.65	
С	0.90	1.10	
D	0.25	0.50	
G	0.95	BSC	
Н	0.01	0.10	
J	0.10	0.26	
K	0.20	0.60	
М	0 °	10°	
S	2.50	3.00	

SOLDERING FOOTPRINT*

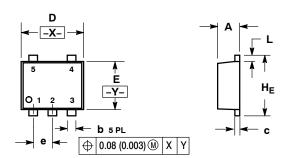


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-553, 5 LEAD

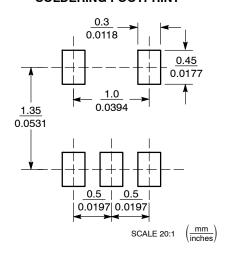
CASE 463B ISSUE C



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
 THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
е		0.50 BSC			0.020 BS0	
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.55	1.60	1.65	0.061	0.063	0.065

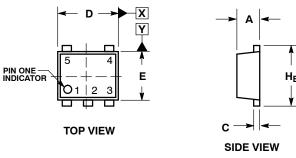
SOLDERING FOOTPRINT*

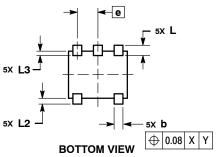


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E





NOTES:

- NOTES:

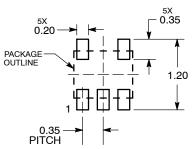
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF THE BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.34	0.37	0.40	
b	0.10	0.15	0.20	
С	0.07	0.12	0.17	
D	0.95	1.00	1.05	
E	0.75	0.80	0.85	
е	0.35 BSC			
HE	0.95	1.00	1.05	
L	0.175 REF			
L2	0.05	0.10	0.15	
L3			0.15	

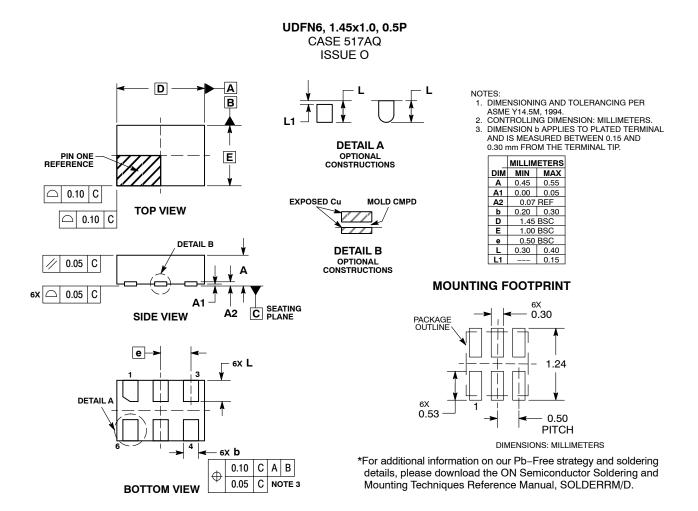
SOLDERING FOOTPRINT*



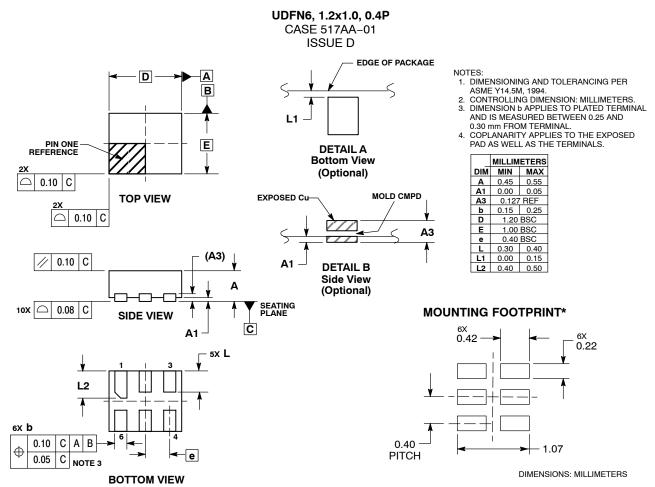
DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

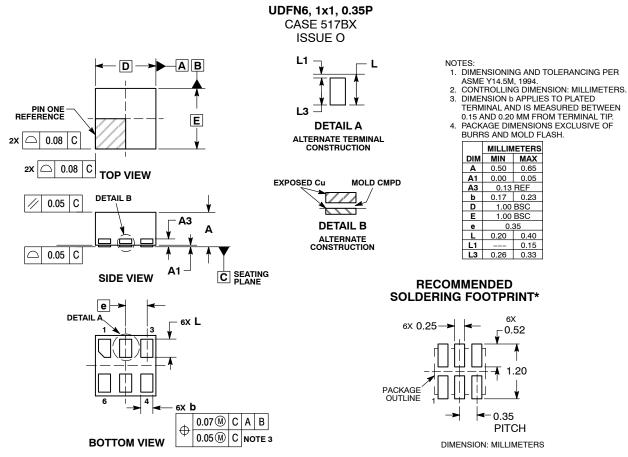


PACKAGE DIMENSIONS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS



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